

(19) World Intellectual Property
Organization
International Bureau



(43) International Publication Date
23 June 2005 (23.06.2005)

PCT

(10) International Publication Number
WO 2005/057654 A3

(51) International Patent Classification⁷: **H01L 23/485**,
21/60

(21) International Application Number:
PCT/IB2004/052628

(22) International Filing Date: 1 December 2004 (01.12.2004)

(25) Filing Language: English

(26) Publication Language: English

(30) Priority Data:
03104621.2 10 December 2003 (10.12.2003) EP

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DK, DM, DZ, EC, EE, EG, ES, FI, GB, GD, GE, GH, GM,
HR, HU, ID, IL, IN, IS, JP, KE, KG, KP, KR, KZ, LC, LK,

LR, LS, LT, LU, LV, MA, MD, MG, MK, MN, MW, MX, MZ,
NA, NI, NO, NZ, OM, PG, PH, PL, PT, RO, RU, SC, SD,
SE, SG, SK, SL, SY, SZ, TJ, TM, TN, TR, TT, TZ, UA, UG,
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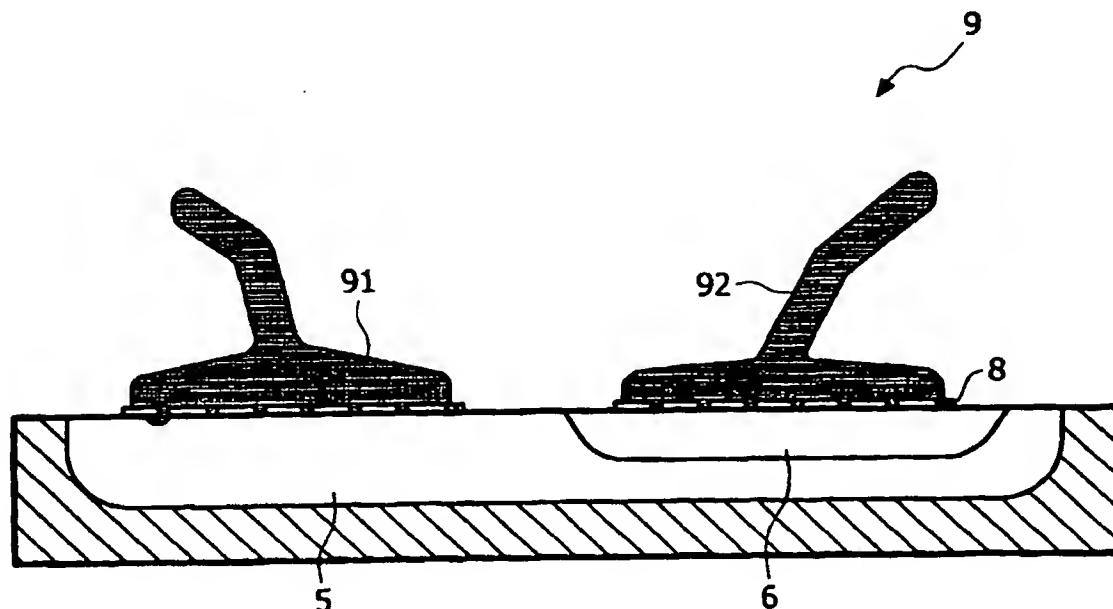
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(81) Designated States (unless otherwise indicated, for every
kind of national protection available): AE, AG, AL, AM,
AT, AU, AZ, BA, BB, BG, BR, BW, BY, BZ, CA, CH, CN,
CO, CR, CU, CZ, DE, DK, DM, DZ, EC, EE, EG, ES, FI,
GB, GD, GE, GH, GM, HR, HU, ID, IL, IN, IS, JP, KE,
KG, KP, KR, KZ, LC, LK, LR, LS, LT, LU, LV, MA, MD,
MG, MK, MN, MW, MX, MZ, NA, NI, NO, NZ, OM, PG,

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(54) Title: WIRE-BONDED SEMICONDUCTOR COMPONENT WITH REINFORCED INNER CONNECTION METALLIZA-
TION



(57) Abstract: A semiconductor component comprising a semiconductor chip (2) made of a doped silicon substrate, which chip is doped into a semiconductor device and structured, and comprises an inner connection metallization (7) in a contact window, and said inner connection metallization of said semiconductor chip is connected to the respective outer connection metallization by a wire bond connection (9), characterized in that the inner connection metallization comprises a reinforcing system (8) having an open grid structure on the doped silicon substrate.



PH, PL, PT, RO, RU, SC, SD, SE, SG, SK, SL, SY, TJ, TM,
TN, TR, TT, TZ, UA, UG, US, UZ, VC, VN, YU, ZA, ZM,
ZW.

Published:

- with international search report
- before the expiration of the time limit for amending the claims and to be republished in the event of receipt of amendments

(84) **Designated States** (unless otherwise indicated, for every kind of regional protection available): ARIPO (BW, GH, GM, KE, LS, MW, MZ, NA, SD, SL, SZ, TZ, UG, ZM, ZW), Eurasian (AM, AZ, BY, KG, KZ, MD, RU, TJ, TM), European (AT, BE, BG, CH, CY, CZ, DE, DK, EE, ES, FI, FR, GB, GR, HU, IE, IS, IT, LT, LU, MC, NL, PL, PT, RO, SE, SI, SK, TR), OAPI (BF, BJ, CF, CG, CI, CM, GA, GN, GQ, GW, ML, MR, NE, SN, TD, TG).

(88) **Date of publication of the international search report:**
4 August 2005

For two-letter codes and other abbreviations, refer to the "Guidance Notes on Codes and Abbreviations" appearing at the beginning of each regular issue of the PCT Gazette.